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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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HVU363A

Variable Capacitance Diode for TV tuner

RENESAS

ADE-208-234B(Z)

Rev. 2 Nov. 1998

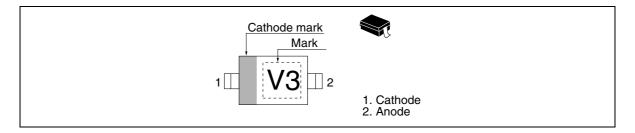
Features

- High capacitance ratio.(n=15.0Typ)
- Low series resistance (rs= 0.75Ω max) and good C-V linearity.
- Ultra small Resin Package (URP) is suitable for surface mount design.

Ordering Information

Туре No.	Laser Mark	Package Code
HVU363A	V3	URP

Pin Arrangement



HVU363A

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit	
Peak reverse voltage	V _{RM} ^{*1}	35	V	
Reverse voltage	V _R	32	V	
Junction temperature	Tj	125	°C	
Storage temperature	Tstg	-55 to +125	°C	

Notes 1. RL=10k Ω

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse voltage	V _R	32	_	_	V	$I_{_{R}} = 1\mu A$
Reverse current	I _{R1}	_	_	10	nA	$V_{_{R}} = 30V$
	I _{R2}	_	_	100	_	V _R = 30V, Ta =60°C
Capacitance	C ₁	34.65	_	42.35	pF	$V_{_{R}} = 1V, f = 1 MHz$
	C ₂₈	2.361	_	2.754		$V_{_{\mathrm{R}}} = 28V, f = 1 \text{ MHz}$
Capacitance ratio	n	13.5	15.0	_	_	C ₁ / C ₂₈
Series resistance	r _s	_	_	0.75	Ω	C=14pF, f = 470 MHz
Matching error	$\Delta C/C^{*1}$	_	_	2.0	%	$V_{_{ m R}}$ = 1 to 28V , f = 1 MHz
Linealty factor *2	_	—	-1.2	—	—	ΔlogC / ΔlogV

 Notes
 1. C.C system (Continuous Connected taping system) enable to make any 10 pcs of ΔC/C continuous in a reel , expect extention to another group.

 Calculate Matching Error,

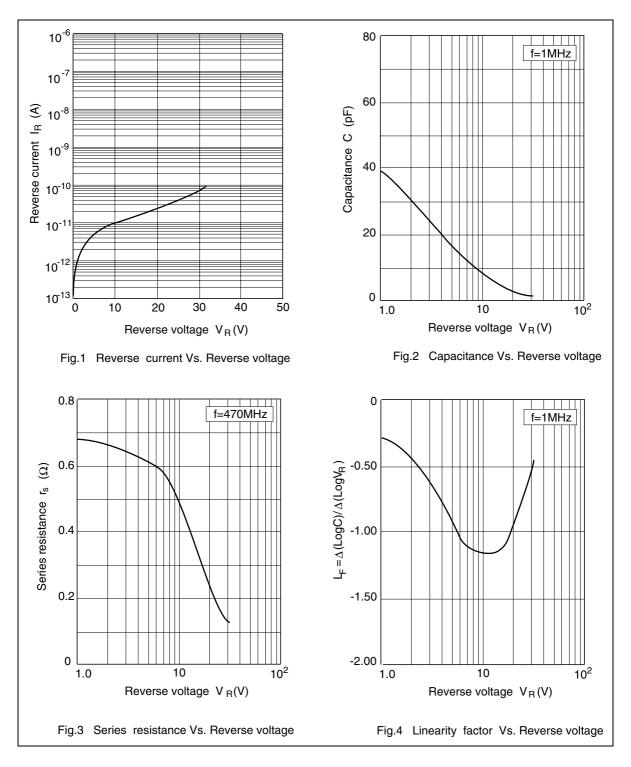
(Cmax-Cmin)

ΔC/C= _____ x 100 (%)

Notes 2. Calculate LF ($\Delta logC / \Delta logV$) at VR = 1 througn 28V , f = 1 MHz .(Reference Value)

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Main Characteristic

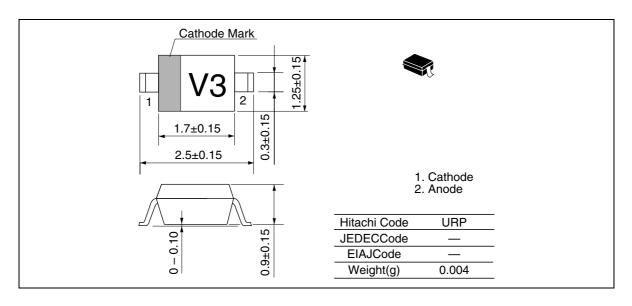


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HVU363A

Package Dimensions

Unit : mm





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Sales Offices



Hitachi. Ltd.

Semiconductor & Integrated Circuits Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: (03) 3270-2111 Fax: (03) 3270-5109

Hitachi Europe Ltd.

URL	NorthAmerica Europe Asia	÷	http://semiconductor.hitachi.com/ http://www.hitachi-eu.com/hel/ecg http://sicapac.hitachi-asia.com
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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive San Jose, CA 95134 Tel: <1> (408) 433-1990 Maidenhead

Electronic Components Group Whitebrook Park Lower Cookham Road Fax: <1>(408) 433-0223 Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 585200

> Hitachi Europe GmbH Electronic Components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00 Singapore 049318 Tel: <65>-538-6533/538-8577 Fax : <65>-538-6933/538-3877 URL : http://www.hitachi.com.sg

Hitachi Asia Ltd (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road Hung-Kuo Building Taipei (105), Taiwan Tel: <886>-(2)-2718-3666 Fax : <886>-(2)-2718-8180 Telex : 23222 HAS-TP URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower World Finance Centre Harbour City, Canton Road Tsim Sha Tsui, Kowloon Hong Kong Tel : <852>-(2)-735-9218 Fax : <852>-(2)-730-0281 URL : http://semiconductor.hitachi.com.hk

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